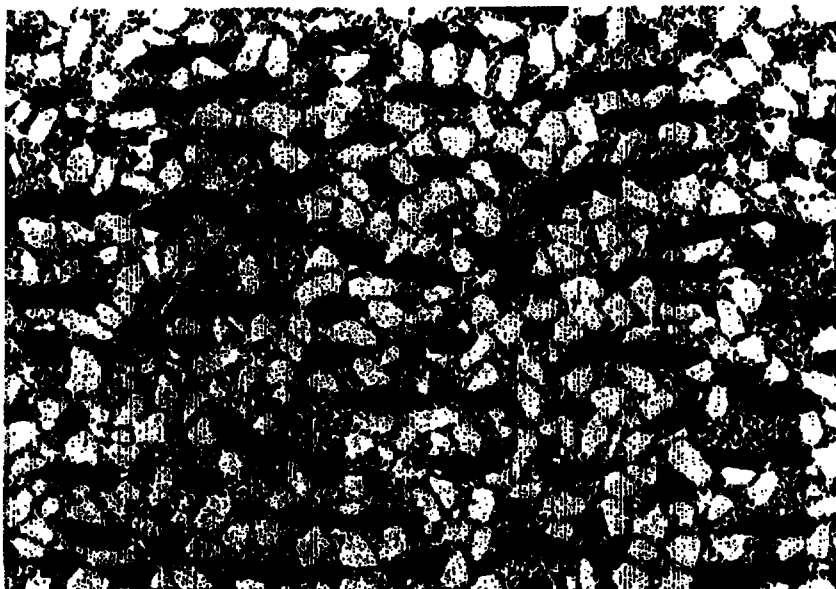




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(54) Title: NOVEL SILICON CARBIDE DUMMY WAFER
100 μ m**(57) Abstract**

The present invention relates to an unsiliconized or siliconized wafer consisting essentially of recrystallized silicon carbide, the wafer having a diameter of at least 150 mm and a thickness of between 0.5 and 2 mm, and having a porosity or free silicon content between 15 v/o and 43 v/o.